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We claim:

- 1 1. A high voltage field-effect transistor (HVFET) comprising:
 - 2 a substrate of a first conductivity type;
 - 3 a first region of a second conductivity type disposed within the substrate;
 - 4 a source diffusion region of the second conductivity type disposed in the
 - 5 substrate spaced-apart from the first region, a channel region being formed in the
 - 6 substrate between the source diffusion region and the first region;
 - 7 a source electrode connected to the source diffusion region;
 - 8 a drain diffusion region of the second conductivity type disposed within the
 - 9 first region;
 - 10 a drain electrode connected to the drain diffusion region;
 - 11 a buried region of the first conductivity type disposed within the first
 - 12 region, a first conduction channel being formed above the buried region and a
 - 13 second conduction channel being formed below the buried region, the buried
 - 14 region being spaced-apart from the drain diffusion region; and
 - 15 an insulated gate formed over the channel region.

- 1 2. The HVFET according to claim 1 further comprising:

- 2 a second region of the first conductivity type disposed within the substrate,
- 3 the source diffusion region being disposed within the second region.

- 1 3. The HVFET according to claim 2 further comprising

- 2 a third region of the first conductivity type disposed in the second region
- 3 adjacent to the source diffusion region.

1 4. The HVFET according to claim 1 wherein the buried region is
2 connected to the substrate.

1 5. The HVFET of claim 1 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 6. The HVFET according to claim 1 further comprising:
2 a second buried region of the first conductivity type disposed within the
3 substrate beneath the source diffusion region.

1 7. The HVFET according to claim 6 wherein the second buried region
2 extends laterally from the source diffusion region under the channel region.

1 8. The HVFET according to claim 1 wherein the first and second
2 conductivity types are p-type and n-type, respectively.

1 9. The HVFET according to claim 1 wherein the buried region includes
2 one or more openings that connect the first and second conduction channels.

1 10. The HVFET according to claim 1 wherein the source and drain
2 electrodes include field plate members.

1 11. The HVFET according to claim 1 wherein the buried region comprises a
2 plurality of buried layers that form a corresponding plurality of conduction
3 channels.

1 12. A high voltage field-effect transistor (HVFET) comprising:
2 a substrate of a first conductivity type;
3 a first region of a second conductivity type disposed within the substrate;
4 a source diffusion region disposed in the substrate spaced-apart from the
5 first region, an IGFET channel region being formed between the source diffusion
6 region and the first region;
7 a drain diffusion region disposed in the first region;
8 a buried region of said first conductivity type disposed within the first
9 region, the buried region forming JFET channels within the first region, one JFET
10 channel being formed above the buried region and another JFET channel below
11 the buried region, the buried region being spaced-apart from the drain diffusion
12 region;
13 an insulated gate formed above the IGFET channel region.

14.1 13. The HVFET according to claim 12 wherein the first region has a first
14.2 surface that borders a surface of the substrate.

15.1 14. The HVFET according to claim 12 further comprising:
16.2 a second buried region of the first conductivity type disposed beneath the
17.3 source diffusion region.

18.1 15. The HVFET according to claim 14 wherein the second buried region
19.2 extends laterally under the IGFET channel region.

20.1 16. The HVFET according to claim 12 wherein the buried region comprises
21.2 a plurality of buried layers that form a corresponding plurality of JFET channels.

1 17. The HVFET according to claim 12, further comprising:
2 a second region of the first conductivity type disposed in the substrate
3 adjacent to the source diffusion region.

1 18. The HVFET according to claim 12, further comprising:
2 a source electrode connected to the source diffusion region; and
3 a drain electrode connected to the drain diffusion region.

1 19. The HVFET according to claim 18 wherein the source and drain
2 electrodes include field plate members.

1 20. The HVFET according to claim 12 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 21. The HVFET according to claim 12 wherein the first region is disposed in
2 an epitaxial layer.

1 22. The HVFET according to claim 12 wherein the buried region includes
2 one or more openings that connect the one and the another of the JFET
3 channels.

1 23. The HVFET according to claim 12 wherein the first and second
2 conductivity types are p-type and n-type, respectively.

1 24. The HVFET according to claim 12 wherein the source diffusion region
2 has a source fingertip area, and the first region has a pair of drain fingertips

3 areas inter-digitated with the source fingertip area, the drain diffusion region
4 being disposed in the pair of drain fingertip areas of the first region.

1 25. The HVFET according to claim 24 further comprising a buffer region
2 disposed between the source diffusion region and the first region about the
3 source fingertip area, the buffer region being substantially wider than the IGFET
4 channel region.

5 26. A high voltage field-effect transistor (HVFET) comprising:
6 a substrate of a first conductivity type;
7 a first region of a second conductivity type disposed in the substrate, the
8 first region having an above region, a below region and a lateral boundary;

9 at least one buried region of the first conductivity type sandwiched within
the first region between the above and below regions;

10 a source diffusion region of the second conductivity type disposed in the
11 substrate, an IGFET channel region being formed between the source diffusion
12 region and the first region;

13 a drain diffusion region of said second conductivity type disposed in the
14 first region spaced-apart from the at least one buried region;
15 an insulated gate formed over the IGFET channel region.

16 27. The HVFET according to claim 26 wherein the at least one buried
17 region extends beyond the lateral boundary of the first region into the substrate.

18 28. The HVFET of claim 26 further comprising:

19 a source electrode connected to the source diffusion region; and

20 a drain electrode connected to the drain diffusion region.

1 29. The HVFET of claim 28 wherein the source and drain electrodes each
2 include a field plate member.

1 30. The HVFET of claim 26 wherein the at least one buried region is
2 spaced-apart from the lateral boundary.

1 31. The HVFET according to claim 26 wherein the first and second
2 conductivity types are p-type and n-type, respectively.

1 32. The HVFET according to claim 26 wherein the source diffusion region
2 has a source fingertip area and the first region has a pair of drain fingertip areas
3 inter-digitated with the source fingertip area.

1 33. The HVFET according to claim 32 further comprising a buffer region
2 disposed between the source diffusion region and the first region about the
3 source fingertip area, the buffer region being substantially wider than the IGFET
4 channel region.

1 34. The HVFET according to claim 26 wherein the at least one buried
2 region comprises a plurality of buried layers which form a corresponding plurality
3 of JFET conduction channels.

1 35. The HVFET according to claim 26 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 36. The HVFET according to claim 26 wherein the first region is disposed in
2 an epitaxial layer.

1 37. The HVFET according to claim 26 wherein the at least one buried
2 region includes one or more openings that connect the above and below regions.

1 38. The HVFET according to claim 26 wherein the at least one buried
2 region is connected to the substrate.

3 39. A high voltage field-effect transistor (HVFET) comprising:
4 a substrate of a first conductivity type;
5 a first region of a second conductivity type;
6 a source diffusion region of the second conductivity type disposed in the
7 substrate spaced-apart from the first region to form an IGFET channel region
8 therebetween;
9 a drain diffusion region disposed in the first region;
10 a first plurality of buried layers of the first conductivity type disposed within
11 the first region spaced-apart from the drain diffusion region, the first plurality of
12 buried layers forming an/associated plurality of JFET channels in the first region;
13 an insulating layer disposed over the substrate; and
14 a gate overlying an area of the insulating layer above the IGFET channel
15 region.

1 40. The HVFET according to claim 39 further comprising:
2 a second plurality of buried layers of the first conductivity type disposed
3 beneath the source diffusion region.

1 41. The HVFET according to claim 40 wherein the second plurality of buried
2 layers extend under the IGFET channel region.

1 42. The HVFET according to claim 39 further comprising:
2 a second region of the first conductivity type disposed in the substrate
3 adjacent the source diffusion region.

1 43. The HVFET according to claim 39 further comprising:
2 a source electrode connected to the source diffusion region; and
3 a drain electrode connected to the drain diffusion region.

1 44. The HVFET according to claim 43 wherein the source electrode
2 includes a first field plate member that extends over the gate.

1 45. The HVFET according to claim 44 wherein the drain electrode includes
2 a second field plate member.

1 46. The HVFET according to claim 39 wherein each of the first plurality of
2 buried regions includes one or more openings that connect adjoining ones of the
3 JFET channels.

1 47. The HVFET according to claim 39 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 48. The HVFET according to claim 39 wherein the first region comprises an
2 epitaxial layer disposed on the substrate.

1 49. The HVFET according to claim 39 wherein the first region comprises a
2 well region disposed in the substrate.

1 50. A high voltage field-effect transistor (HVFET) comprising:
2 a substrate of a first conductivity type;
3 a source diffusion region of a second conductivity type disposed in the
4 substrate, the source diffusion region having a source fingertip area;
5 a first region of the second conductivity type disposed in the substrate
6 spaced-apart from the source diffusion region with an IGFET channel region
7 being formed therebetween, the first region having a pair of drain fingertips areas
8 inter-digitated with the source fingertip area;
9 a drain diffusion region of the second conductivity type disposed in the first
10 region,
11 a buffer area formed between the source diffusion region and the first
12 region adjacent the source fingertip area, the buffer area being substantially
13 wider than the IGFET channel region;
14 an insulated gate disposed above the IGFET channel region;
15 at least one buried layer of the first conductivity type disposed within the
16 first region, the at least one buried layer forming two or more JFET channels in
17 the first region.

1 51. The HVFET of claim 50 further comprising:
2 a drain electrode that includes a drain field plate which overlaps a portion
3 of the first region.

1 52. The HVFET of claim 50 further comprising:

2 a source electrode that includes a source field plate which extends over
3 the insulated gate.

1 53. The HVFET of claim 50 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 54. The HVFET according to claim 50 wherein the at least one buried layer
2 comprises a plurality of buried layers forming an associated plurality of JFET
3 channels in the first region.

1 55. The HVFET according to claim 50 further comprising:
2 a second plurality of buried layers of the first conductivity type disposed
3 beneath the source diffusion region.

1 56. The HVFET according to claim 55 wherein the second plurality of buried
2 layers extends beneath the IGFET channel region.

1 57. The HVFET according to claim 50 wherein the at least one buried layer
2 is connected to the substrate.

1 58. A high voltage field-effect transistor (HVFET) comprising:
2 a substrate of a first conductivity type;
3 a first region of a second conductivity type;
4 a second region of the first conductivity type disposed in the first region;

5 a source diffusion region of the second conductivity type disposed in the
6 second region, a channel region being formed between the first region and the
7 source diffusion region;

8 a drain diffusion region of the second conductivity type disposed in the first
9 region;

10 a buried region of the first conductivity type sandwiched within the first
11 region to form first and second JFET channels therein, the first JFET channel
12 being formed above the buried region and the second JFET channel being
13 formed below the buried region, the buried region being spaced-apart from the
14 drain diffusion region;

15 an insulated gate formed over the channel region.

59. The HVFET according to claim 58 further comprising:

2 a source electrode connected to the source diffusion region; and
3 a drain electrode connected to the drain diffusion region.

59. The HVFET according to claim 59 wherein the drain electrode includes

2 a field plate member that extends over a portion of the first region between the
3 drain diffusion region and the buried region.

1 61. The HVFET according to claim 58 wherein the first region comprises an
2 epitaxial layer disposed on the substrate.

1 62. The HVFET according to claim 58 wherein the first region comprises a
2 well region disposed in the substrate.

1 63. The HVFET according to claim 58 wherein the first conductivity type is
2 p-type and the second conductivity type is n-type.

1 64. The HVFET of claim 58 further comprising:
2 a tap diffusion region of the second conductivity type disposed in the first
3 region near a perimeter boundary of the first region.

1 65. The HVFET according to claim 58 wherein the buried region comprises
2 a plurality of buried layers forming an associated plurality of JFET channels in the
3 first region.

1 66. The HVFET according to claim 58 further comprising:
2 a second buried region of the first conductivity type disposed beneath the
3 source diffusion region.

1 67. The HVFET according to claim 66 wherein the second buried region
2 extends beneath the channel region.

1 68. A high voltage field-effect transistor (HVFET) comprising:
2 a substrate of a first conductivity type;
3 a first region of a second conductivity type disposed in the substrate, the
4 first region having a laterally extended portion that forms a lateral boundary with
5 the substrate;
6 a drain diffusion region of the second conductivity type disposed in the first
7 region and separated from the lateral boundary by the laterally extended portion;
8 a second region of the first conductivity type disposed in the substrate;

9 a source diffusion region of the second conductivity type disposed in the
10 second region, a channel region being formed between the source diffusion
11 region and the lateral boundary;
12 an insulated gate disposed above the channel region;
13 a buried region of the first conductivity type sandwiched within the laterally
14 extended portion of the first region to form a junction field-effect device in which
15 current flows in the first region both above and below the buried region.

1 69. The HVFET according to claim 68 wherein the insulated gate extends
2 laterally over the substrate from the source diffusion region to the lateral
3 boundary.

4 70. The HVFET according to claim 68 wherein the second region is spaced-
5 apart from the lateral boundary.

6 71. The HVFET according to claim 68 wherein the first region comprises an
7 epitaxial layer.

8 72. The HVFET according to claim 68 wherein the buried region is
9 connected to the substrate.

10 73. The HVFET according to claim 68 wherein the buried region is spaced-
11 apart from the lateral boundary.

12 74. The HVFET according to claim 68 wherein the first and second
13 conductivity types are p-type and n-type, respectively.

1 75. The HVFET according to claim 68 wherein the first and second
2 conductivity types are n-type and p-type, respectively.

1 76. The HVFET according to claims 68, 69, 70, 71, 72, 73, 74 or 75 further
2 comprising:

3 an additional diffusion region of the first conductivity type disposed in the
4 second region adjacent the source diffusion region.

1 77. A high voltage field-effect transistor (HVFET) comprising:

2 a substrate of a first conductivity type;

3 a first region of a second conductivity type disposed in the substrate, the
4 first region having a laterally extended portion that forms a lateral boundary with
5 the substrate;

6 a drain diffusion region of the second conductivity type disposed in the first
7 region and separated from the lateral boundary by the laterally extended portion;

8 a source diffusion region of the second conductivity type disposed in the
9 substrate and spaced-apart from the lateral boundary of the first region, a
10 channel region being formed between the source diffusion region and the lateral
11 boundary;

12 an insulated gate disposed above the channel region;

13 a first buried layer of the first conductivity type disposed in the substrate
14 beneath the source diffusion region;

15 a second buried layer of the first conductivity type sandwiched within the
16 laterally extended portion of the first region and spaced-apart from the lateral
17 boundary so as to act as an effective gate controlling dual current channels in the
18 first region both above and below the second buried layer.

1 78. The HVFET according to claim 77 wherein the insulated gate extends
2 laterally over the substrate from the source diffusion region to the lateral
3 boundary.

1 79. The HVFET according to claim 77 wherein the insulated gate extends
2 laterally over the substrate from the source diffusion region to the second buried
3 layer.

1 80. The HVFET according to claim 77 wherein the first buried region is
2 spaced-apart from the lateral boundary.

1 81. The HVFET according to claim 77 wherein the first and second
2 conductivity types are p-type and n-type, respectively.

1 82. The HVFET according to claim 77 wherein the first and second
2 conductivity types are n-type and p-type, respectively.

1 83. The HVFET according to claims 77, 78, 79, 80, 81, or 82 further
2 comprising
3 an additional diffusion region of the first conductivity type disposed in the
4 substrate adjacent the source diffusion region.

1 84. A high voltage field-effect transistor (HVFET) comprising:
2 a substrate of a first conductivity type;
3 a first region of a second conductivity type disposed in the substrate, the
4 first region having a laterally extended portion that forms a lateral boundary with
5 the substrate;

6 a drain diffusion region of the second conductivity type disposed in the first
7 region and separated from the lateral boundary by the laterally extended portion;
8 a source diffusion region of the second conductivity type disposed in the
9 substrate and spaced-apart from the lateral boundary, an IGFET channel region
10 being formed between the source diffusion region and the lateral boundary;
11 an insulated gate disposed above the IGFET channel region;
12 a buried layer of the first conductivity type disposed in the substrate
13 spaced-apart from the drain diffusion region, the buried layer extending through
14 the laterally extended portion of the first region to beneath the source diffusion
15 region, the buried layer dividing the first region into an above region and a below
16 region, the buried layer having one or more openings which connect the above
17 and below regions.

85. The HVFET according to claim 84 further comprising:

an additional diffusion region of the first conductivity type disposed in the
substrate adjacent the source diffusion region.

86. The HVFET according to claim 84 wherein the buried layer extends beneath

the drain diffusion region, at least one of the one or more openings being positioned
close to the drain diffusion region.

87. The HVFET according to claim 84 wherein the one or more openings are

hexagonal, square, circular, or triangular in shape.

88. The HVFET according to claim 84 wherein the one or more openings are

circular in shape.

1 89. The HVFET according to claim 84 wherein the one or more openings are
2 arranged in a pattern.

1 90. The HVFET according to claim 89 wherein the pattern is a checkerboard
2 pattern.

1 91. The HVFET according to claim 89 wherein the pattern creates buried layer
2 sections that deplete in a three-dimensional fashion.

1 92. The HVFET according to claim 91 wherein each of the buried layer sections
2 are spherical.

3 93. A high voltage field-effect transistor (HVFET) comprising:
4 a substrate of a first conductivity type;
5 a epitaxial layer of a second conductivity type disposed on the substrate;
6 a diffusion region of the first conductivity type disposed in the epitaxial
7 layer, a junction being formed between the diffusion region and the epitaxial
8 layer;
9 a drain region of the second conductivity type disposed in the epitaxial
10 layer and separated from the junction by a portion of the epitaxial layer;
11 a source region of the second conductivity type disposed in the diffusion
12 region, the source region being spaced-apart from the junction, a channel region
13 being formed between the source region and the junction;
14 an insulated gate disposed above the channel region;
15 a buried layer of the first conductivity type disposed within the portion of
16 the epitaxial layer spaced-apart from the drain diffusion region, the buried layer

15 acting as an effective gate to control dual current channels formed above and
16 below the buried layer.

1 94. The HVFET according to claim 93 wherein the buried layer is spaced-
2 apart from the junction.

1 95. The HVFET according to claim 93 further comprising:
2 an additional buried layer of the first conductivity type disposed beneath
3 the source region.

1 96. The HVFET according to claim 93 wherein the insulated gate extends
2 laterally over the substrate from the source region to the buried layer.

1 97. The HVFET according to claim 96 wherein the insulated gate overlaps
2 the buried layer.

1 98. The HVFET according to claim 93 wherein the buried layer extends
2 beneath the drain region.

1 99. The HVFET according to claim 93 wherein the buried layer is connected
2 to the substrate.

1 100. The HVFET according to claim 93 wherein the first and second
2 conductivity types are p-type and n-type, respectively.

1 101. The HVFET according to claim 93 further comprising:
2 a source electrode connected to the source region; and

3 a drain electrode connected to the drain region.

1 102. The HVFET according to claims 93, 94, 95, 96, 97, 98, 99, 100 or 101

2 further comprising:

3 an additional diffusion region of the first conductivity type disposed in the

4 diffusion region adjacent the source region.

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